

CMPDM7002A
CMPDM7002AG*

**SURFACE MOUNT
N-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET**



SOT-23 CASE

* Device is **Halogen Free** by design



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPDM7002A and CMPDM7002AG are special versions of the 2N7002 Enhancement-mode N-Channel Field Effect Transistor, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. These special devices offer low $r_{DS(ON)}$ and low $V_{DS(ON)}$.

**MARKING CODES: CMPDM7002A: C702A
CMPDM7002AG*: 702G**

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Drain-Source Voltage
Drain-Gate Voltage
Gate-Source Voltage
Continuous Drain Current
Continuous Source Current (Body Diode)
Maximum Pulsed Drain Current
Maximum Pulsed Source Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{DS} 60
 V_{DG} 60
 V_{GS} 40
 I_D 280
 I_S 280
 I_{DM} 1.5
 I_{SM} 1.5
 P_D 350
 T_J, T_{stg} -65 to +150
 θ_{JA} 357

UNITS

V
V
V
mA
mA
A
A
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

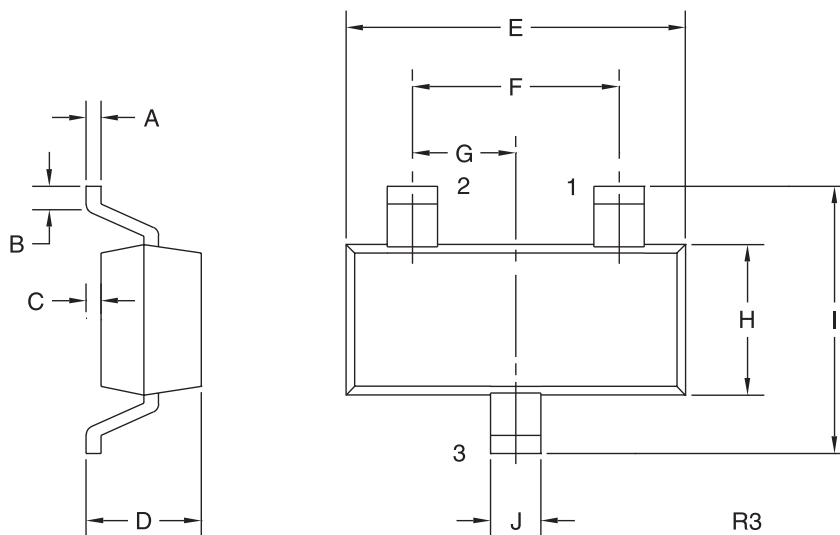
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=20\text{V}, V_{DS}=0$		100	nA
I_{DSS}	$V_{DS}=60\text{V}, V_{GS}=0$		1.0	μA
I_{DSS}	$V_{DS}=60\text{V}, V_{GS}=0, T_J=125^\circ\text{C}$		500	μA
$I_{D(ON)}$	$V_{GS}=10\text{V}, V_{DS}=10\text{V}$	500		mA
BV_{DSS}	$V_{GS}=0, I_D=10\mu\text{A}$	60		V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0	2.5	V
$V_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}$		1.0	V
$V_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}$		0.15	V
V_{SD}	$V_{GS}=0, I_S=400\text{mA}$		1.2	V
$r_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}$		2.0	Ω
$r_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}, T_J=125^\circ\text{C}$		3.5	Ω
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}$		3.0	Ω
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}, T_J=125^\circ\text{C}$		5.0	Ω
gFS	$V_{DS}=10\text{V}, I_D=200\text{mA}$	80		mS
C_{rss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$		5.0	pF
C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$		50	pF
C_{oss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$		25	pF
t_{on}, t_{off}	$V_{DD}=30\text{V}, V_{GS}=10\text{V}, I_D=200\text{mA}, R_G=25\Omega, R_L=150\Omega$		20	ns

R4 (27-January 2010)

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SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Gate
- 2) Source
- 3) Drain

MARKING CODES:

CMPDM7002A: C702A
 CMPDM7002AG*: 702G

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DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

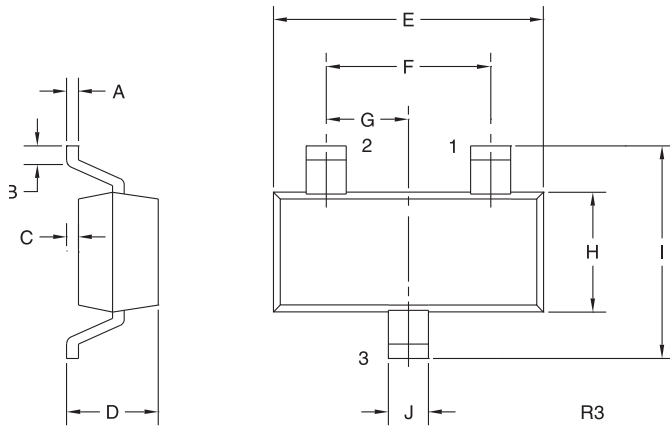
R4 (27-January 2010)

Package Details

SOT-23 Case



Mechanical Drawing



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

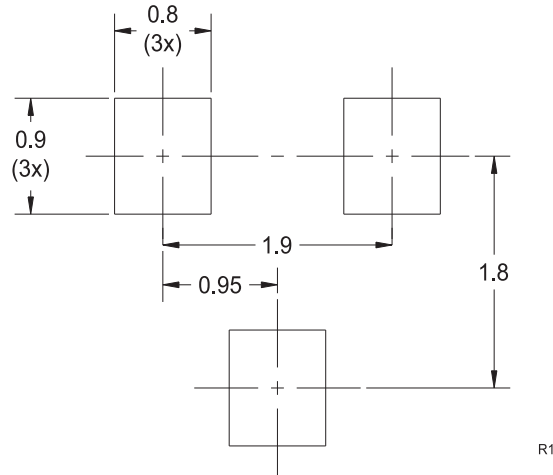
SOT-23 (REV: R3)

Lead Code:

Reference individual device datasheet.

Part Marking: 2-4 Character Alpha/Numeric Code

Mounting Pad Geometry (Dimensions in mm)



R3 (4-March 2010)

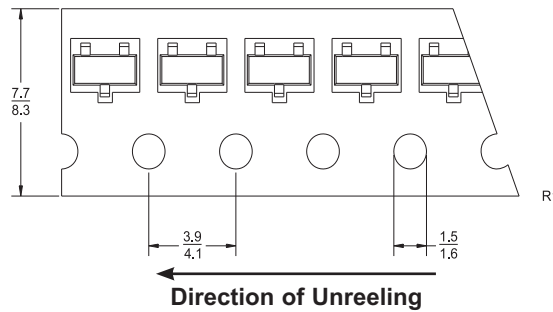
Package Details

SOT-23 Case



Tape Dimensions and Orientation (Dimensions in mm)

Tape Width: 8mm



* Devices are taped in accordance with Electronic Industries Association Standard EIA-481-1-A

Packaging Base

7" Reel = 3,000 pcs.
13" Reel = 10,000 pcs.

Reel Labeling Information

Each reel is labeled with the following information:

Central Part Number, Customer Part Number, Purchase Order Number, Quantity, Lot Number, Date Code, Ship Date and Marking Code.

Reel Packing Information

Reel Size	Reels per Box (Maximum)	Parts per Box (Maximum)	Box Dimensions		Shipping Weight (Max.)	
			INCH	CM	LB	KG
7"	9	27,000	9x9x5	23x23x13	3	2
	18	54,000	9x9x9	23x23x23	6	3
	40	120,000	21x9x9	53x23x23	13	6
	108	324,000	27x9x17	69x23x43	34	16
13"	6	60,000	15x4x15	38x10x38	6	3
	14	140,000	15x15x9	38x38x23	15	7
	26	260,000	15x15x18	38x38x46	28	13

Ordering Information

- For devices taped and reeled on 7" reels, add TR suffix to part number.
- For devices taped and reeled on 13" reels, add TR13 suffix to part number.
- All SMDs are available in small quantities for prototype and manual placement applications.

R3 (4-March 2010)

Material Composition Specification

SOT-23 Case

Pb (lead)-free plating**



Device average mass 8.5 mg

Fluctuation margin +/-10%

Component	Material	Material		Substance	CAS No.	Substance		
		(%wt)	(mg)			(%wt)	(mg)	(ppm)
active device	doped Si	2.71%	0.23	Si	7440-21-3	2.71%	0.23	27,059
bond wire	gold	0.25%	0.02	Au	7440-57-5	0.25%	0.021	2,471
leadframe	alloy 42 w/ silver plating	26.11%	2.22	Fe	7439-89-6	14.99%	1.274	149,882
				Ni	7440-02-0	10.41%	0.885	104,118
				Ag	7440-22-4	0.71%	0.06	7,059
encapsulation*	EMC	68.94%	5.86	silica	7631-86-9	46.87%	3.984	468,706
				epoxy resin	29690-82-2	13.79%	1.172	137,882
				phenol resin	9003-35-4	6.89%	0.586	68,941
				Sb ₂ O ₃	1309-64-4	0.69%	0.059	6,941
				Br	7726-95-6	0.69%	0.059	6,941
	EMC GREEN	68.94%	5.86	silica (fused)	60676-86-0	53.08%	4.512	530,824
				epoxy resin	29690-82-2	6.89%	0.586	68,941
				phenol resin	9003-35-4	6.68%	0.568	66,824
				carbon black	1333-86-4	0.21%	0.018	2,118
				metal hydroxide	1309-42-8	2.07%	0.176	20,706
plating**	tin lead process	2.0%	0.17	Sn	7440-31-5	1.59%	0.135	15,882
				Pb	7439-92-1	0.41%	0.035	4,118
	100% matte tin	2.0%	0.17	Sn	7440-31-5	2.0%	0.17	20,000

*EMC GREEN molding compound is Halogen Free.

**Specify Lead-Free when ordering 100% tin (Pb-free) plating.

Disclaimer

The information provided in this Material Composition data sheet is, to the best of our knowledge, correct. However, there is no guarantee to completeness or accuracy, as some information is derived from data sources outside the company.

R5 (9-March 2010)